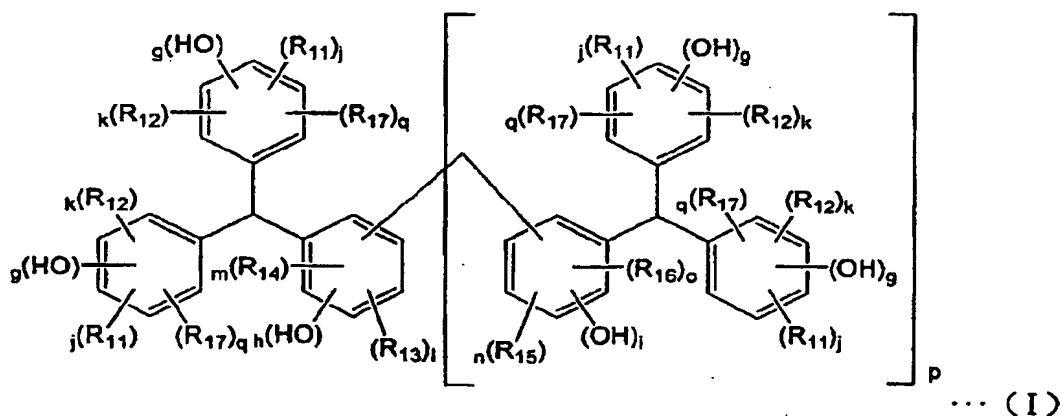## CLAIMS

1.   A base material for a pattern-forming material, comprising a low molecular

weight compound (X1), which is formed from a polyhydric phenol compound (x) that

5   comprises two or more phenolic hydroxyl groups and satisfies conditions (1), (2), and (3)

described below, wherein either a portion of, or all of, said phenolic hydroxyl groups are

protected with acid dissociable, dissolution inhibiting groups:

(1) a molecular weight within a range from 300 to 2,500, (2) a molecular weight

dispersity of no more than 1.5, and (3) an ability to form an amorphous film using a spin

10   coating method.

2.   A base material for a pattern-forming material according to claim 1, wherein said

polyhydric phenol compound (x) is one or more compounds selected from the group

consisting of polyhydric phenol compounds represented by general formulas (I), (II), and
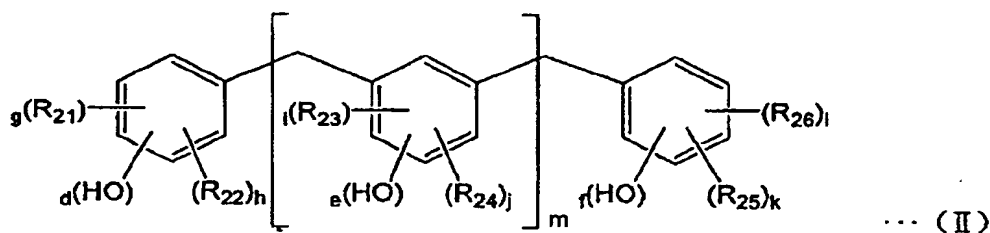
15   (III) shown below:

[Formula 1]

$$\cdots \ (\text{I})$$

[wherein, R_{11} through R_{17} each represent, independently, an alkyl group or aromatic

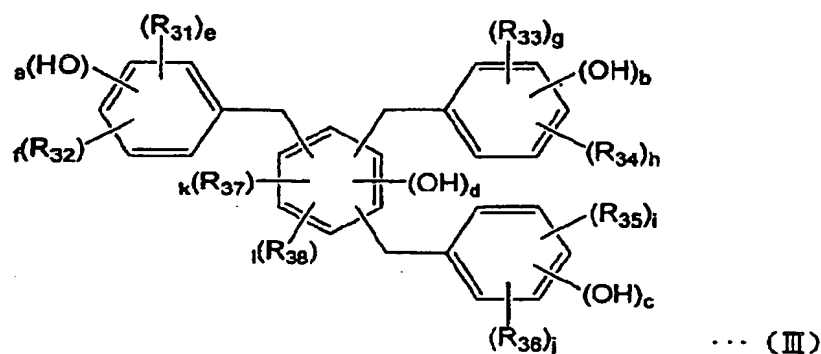hydrocarbon group of 1 to 10 carbon atoms, and these structures may also include a

hetero atom; g and j each represent, independently, an integer of 1 or greater, k and q

each represent either 0 or an integer of 1 or greater, and g+j+k+q is no greater than 5; h is

an integer of 1 or greater, l and m each represent, independently, either 0 or an integer of

1 or greater, and h+l+m is no greater than 4; i is an integer of 1 or greater, n and o each

5   represent, independently, either 0 or an integer of 1 or greater, and i+n+o is no greater

than 4; and p is either 0 or 1],

[Formula 2]

$\cdots$ (II)

[wherein, R_{21} through R_{26} each represent, independently, an alkyl group or aromatic

10   hydrocarbon group of 1 to 10 carbon atoms, and these structures may also include a

hetero atom; d and g each represent, independently, an integer of 1 or greater, h

represents either 0 or an integer of 1 or greater, and d+g+h is no greater than 5; e

represents an integer of 1 or greater, i and j each represent, independently, either 0 or an

integer of 1 or greater, and e+i+j is no greater than 4; f and k each represent,

15   independently, an integer of 1 or greater, l represents either 0 or an integer of 1 or greater,

and f+k+l is no greater than 5; and m is an integer from 1 to 20],

[Formula 3]

$$a(HO) \quad (R_{31})_e \quad (R_{33})_g \quad (OH)_b$$

$$f(R_{32}) \quad (R_{34})_h$$

$$k(R_{37}) \quad (OH)_d$$

$$l(R_{38}) \quad (R_{35})_i$$

$$(OH)_c$$

$$(R_{36})_j \qquad \cdots \quad (III)$$

[wherein, R_{31} through R_{38} each represent, independently, an alkyl group or aromatic hydrocarbon group of 1 to 10 carbon atoms, and these structures may also include a

5   hetero atom; a and e each represent, independently, an integer of 1 or greater, f represents either 0 or an integer of 1 or greater, and a+e+f is no greater than 5; b and h each represent, independently, an integer of 1 or greater, g represents either 0 or an integer of 1 or greater, and b+h+g is no greater than 5; c and i each represent, independently, an integer of 1 or greater, j represents either 0 or an integer of 1 or greater, and c+i+j is no

10   greater than 5; d represents an integer of 1 or greater, k and l each represent, independently, either 0 or an integer of 1 or greater, and d+k+l is no greater than 3].

3.   A positive resist composition, comprising a base material component (A), which contains acid dissociable, dissolution inhibiting groups and displays increased alkali

15   solubility under action of acid, and (B) an acid generator that generates acid on exposure, wherein

    said base material component (A) is a base material for a pattern-forming material according to claim 1.

4.   A positive resist composition, comprising a base material component (A), which contains acid dissociable, dissolution inhibiting groups and displays increased alkali solubility under action of acid, and (B) an acid generator that generates acid on exposure, wherein

5   said base material component (A) is a base material for a pattern-forming material according to claim 2.

5.   A positive resist composition according to claim 3, further comprising a nitrogen-containing organic compound (D).

10

6.   A method of forming a resist pattern comprising the steps of applying a positive resist composition according to claim 3 to a substrate, conducting a prebake, performing selective exposure, conducting PEB (post exposure baking), and performing alkali developing to form a resist pattern.

15

7.   A method of forming a resist pattern comprising the steps of applying a positive resist composition according to claim 4 to a substrate, conducting a prebake, performing selective exposure, conducting PEB (post exposure baking), and performing alkali developing to form a resist pattern.
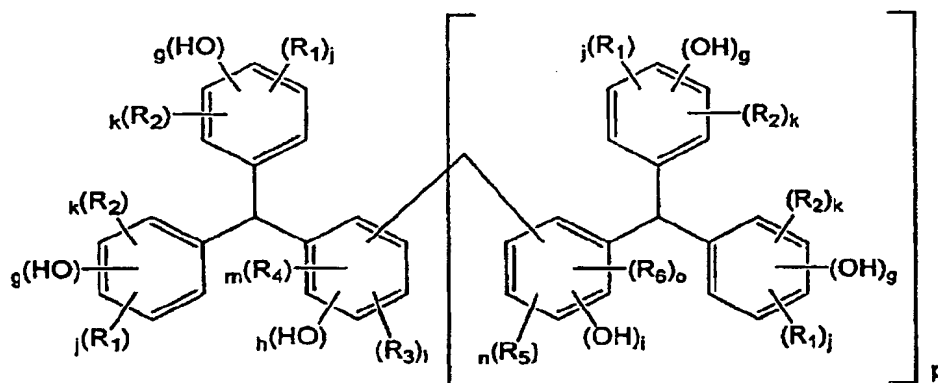
20

8.   A base material for a pattern-forming material, comprising a protected material (Y1), which is formed from a polyhydric phenol compound (y) that comprises two or more phenolic hydroxyl groups and has a molecular weight within a range from 300 to 2,500, in which either a portion of, or all of, said phenolic hydroxyl groups are protected

25   with acid dissociable, dissolution inhibiting groups, wherein a proportion within said

base material of an unprotected material (Y2), in which said phenolic hydroxyl groups of said polyhydric phenol compound (y) are not protected with acid dissociable, dissolution inhibiting groups, is no more than 60% by weight.

5   9.   A base material for a pattern-forming material according to claim 8, wherein a molecular weight dispersity (Mw/Mn) of said polyhydric phenol compound (y) is no more than 1.5.

10.   A base material for a pattern-forming material according to claim 8, wherein said
10   polyhydric phenol compound (y) is a compound represented by a general formula (I) shown below:

[Formula 4]

$$g(HO), (R_1)_j, k(R_2), k(R_2), g(HO), m(R_4), h(HO), j(R_1), (R_3)_h, j(R_1), (OH)_g, (R_2)_k, (R_2)_k, (R_6)_o, n(R_5), (OH)_i, (R_1)_j, (OH)_g \Big]_p$$

[wherein, R_1 through R_6 each represent, independently, an alkyl group or aromatic
15   hydrocarbon group of 1 to 10 carbon atoms, and these structures may also include a hetero atom; g and j each represent, independently, an integer of 1 or greater, k represents either 0 or an integer of 1 or greater, and g+j+k is no greater than 5; h is an integer of 1 or greater, l and m each represent, independently, either 0 or an integer of 1 or greater, and h+l+m is no greater than 4; i is an integer of 1 or greater, n and o each represent,

independently, either 0 or an integer of 1 or greater, and i+n+o is no greater than 4; and p is either 0 or 1].

11.   A positive resist composition, comprising a base material component (A), which

5   contains acid dissociable, dissolution inhibiting groups and displays increased alkali

solubility under action of acid, and (B) an acid generator that generates acid on exposure, wherein

said base material component (A) is a base material for a pattern-forming material according to claim 8.

10

12.   A positive resist composition, comprising a base material component (A), which

contains acid dissociable, dissolution inhibiting groups and displays increased alkali

solubility under action of acid, and (B) an acid generator that generates acid on exposure, wherein

15   said base material component (A) is a base material for a pattern-forming material

according to claim 10.

13.   A positive resist composition according to claim 11, further comprising a

nitrogen-containing organic compound (D).

20

14.   A method of forming a resist pattern comprising the steps of applying a positive

resist composition according to claim 11 to a substrate, conducting a prebake, performing

selective exposure, conducting PEB (post exposure baking), and performing alkali

developing to form a resist pattern.

25

15.	A method of forming a resist pattern comprising the steps of applying a positive resist composition according to claim 12 to a substrate, conducting a prebake, performing selective exposure, conducting PEB (post exposure baking), and performing alkali developing to form a resist pattern.

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